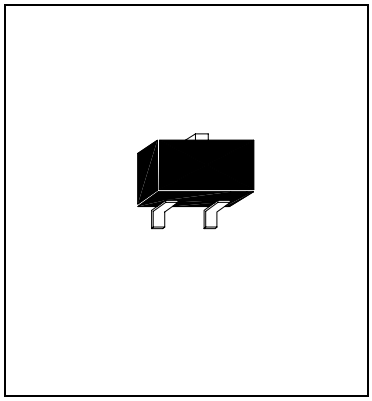
TIGER ELECTRONIC CO.,LTD

MMBT5401LT1

PNP EPITAXIAL PLANAR TRANSISTOR



Description

The MMBT5401LT1 is designed for general purpose applications requiring high breakdown voltages.

Features

- High Collector-Emitter Breakdown Voltage. BVCEO=150V(@ IC=1mA)
- Complements to NPN Type MMBT5551LT1.

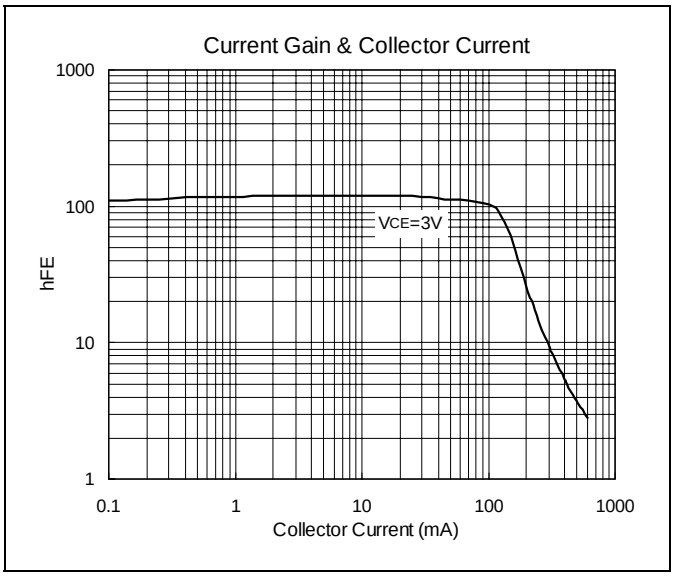
Absolute Maximum Ratings

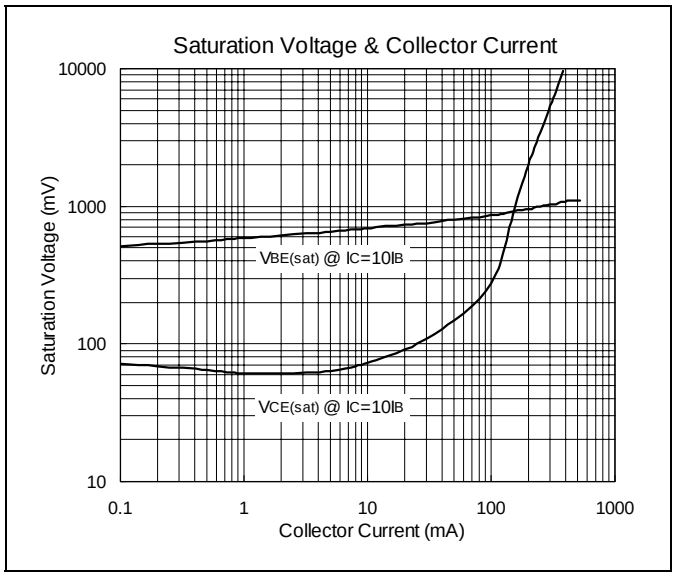
- Maximum Temperatures
  Storage Temperature ..... -55~+150 °C
  Junction Temperature ..... +150°C Maximum
- Maximum Power Dissipation
  Total Power Dissipation (Ta=25°C) ..... 250 mW
- Maximum Voltages and Currents (Ta=25°C)
  VCBO Collector to Base Voltage ..... 160 V
  VCEO Collector to Emitter Voltage ..... 150 V
  VEBO Emitter to Base Voltage ..... 5 V
  IC Collector Current 500mA

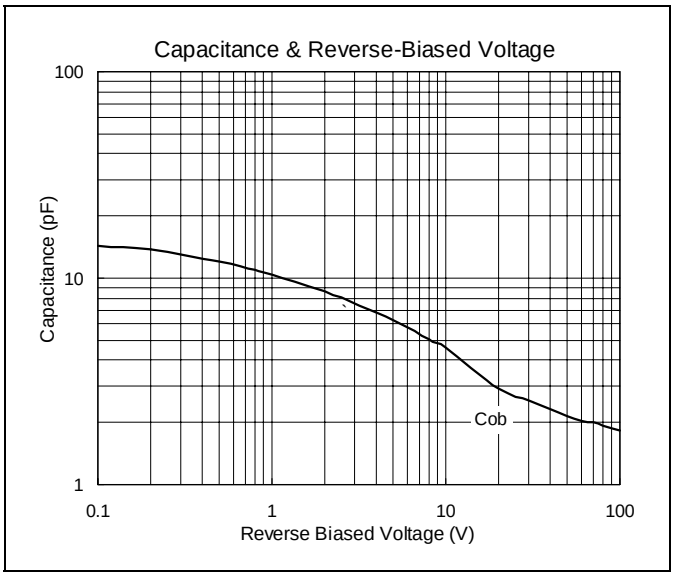
Characteristics (Ta=25°C)

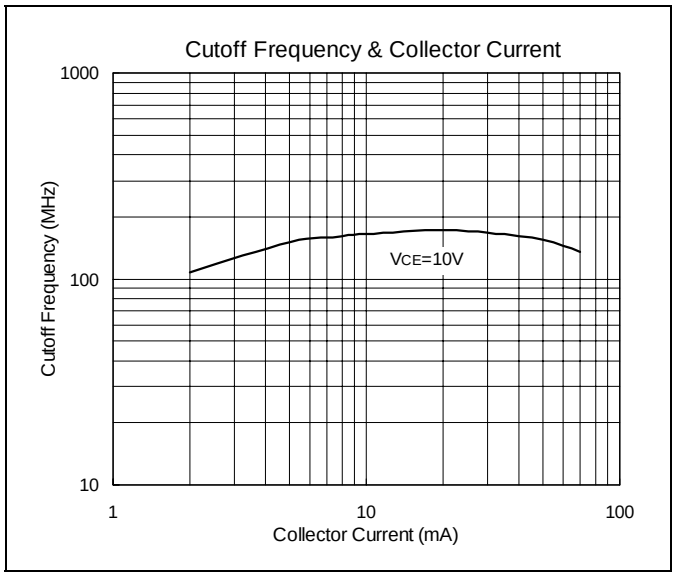
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	160	-	-	V	IC=100uA
BVCEO	150	-	-	V	IC=1mA
BVEBO	5	-	-	V	IE=10uA
ICBO	-	-	50	nA	VCB=120V
VCE(sat)1	-	-	200	mV	IC=10mA, IB=1mA
VCE(sat)2	-	-	500	mV	IC=50mA, IB=5mA
VBE(sat)1	-	-	1	V	IC=10mA, IB=1mA
VBE(sat)2	-	-	1	V	IC=50mA, IB=5mA
hFE1	50	-	-		VCE=5V, IC=1mA
hFE2	60	-	240		VCE=5V, IC=10mA
hFE3	50	-	-		VCE=5V, IC=50mA
fT	100	-	300	MHz	VCE=10V, IC=10mA, f=100MHz
Cob	-	-	6	pF	VCB=10V, f=1MHZ

Characteristics Curve









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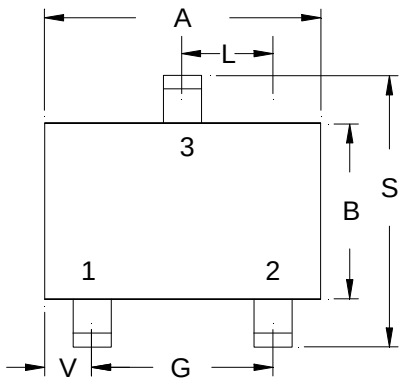
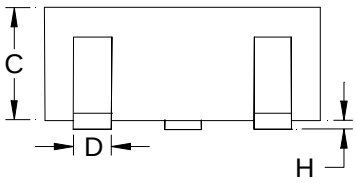
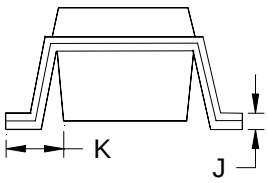
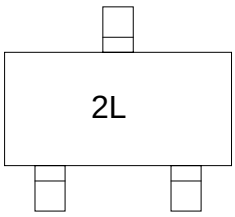
SOT-23 Dimension







Marking :



3-Lead SOT-23 Plastic
Surface Mounted Package

Style : Pin 1.Base 2.Emitter 3.Collector

*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.118	2.80	3.00	J	0.0035	0.0043	0.09	0.11
B	0.0550	0.0630	1.40	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0354	0.0512	0.90	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0886	0.1083	2.25	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	-	0.0040	-	0.10					